

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
80V	9.0mΩ@10V	60A



**合肥矽普半导体**

Siliup Semiconductor Technology Co., Ltd

技术 品质 服务

www.siliup.com

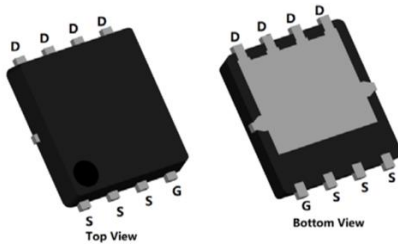
## Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

## Applications

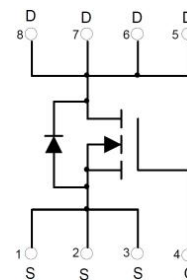
- Power switching application
- DC-DC Converter
- Uninterruptible power supply

## Package



PDFN5X6-8L

## Circuit diagram



## Marking



**SP80N09GHNK**  
\*\*

:Device Code  
:Week Code

## Order Information

Device	Package	Unit/Tape
SP80N09GHNK	PDFN5X6-8L	5000

**Absolute maximum ratings (Ta=25°C, unless otherwise noted)**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	80	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current (Tc=25°C)	$I_D$	60	A
Continuous Drain Current (Tc=100°C)	$I_D$	40	A
Pulse Drain Current Tested	$I_{DM}$	240	A
Single Pulse Avalanche Energy <sup>1</sup>	$E_{AS}$	78	mJ
Power Dissipation (Tc=25°C)	$P_D$	71.4	W
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	1.75	°C/W
Maximum Junction Temperature	$T_J$	-55 to 150	°C
Storage Temperature Range	$T_{STG}$	-55 to 150	°C

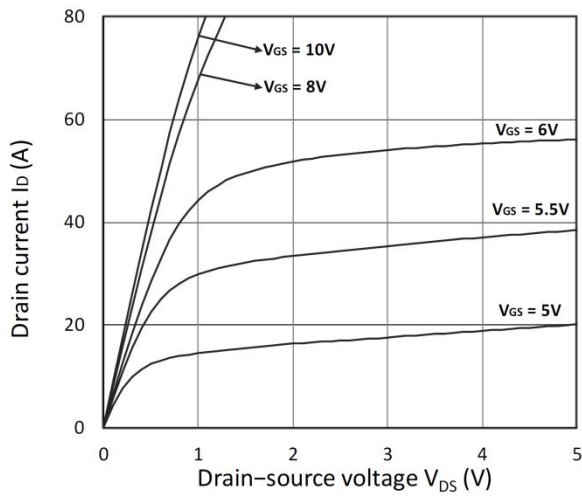
**Electrical characteristics (Ta=25°C, unless otherwise noted)**

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	80	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V	-	-	1	uA
Gate Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.0	3.0	4.0	V
Drain-Source On-state Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	-	9.0	12.5	mΩ
Dynamic Characteristics						
Input Capacitance	C <sub>iss</sub>	VGS=0V, VDS=40V,F=1MHz	-	936	-	pF
Output Capacitance	C <sub>oss</sub>		-	332	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	20	-	
Total Gate Charge	Q <sub>g</sub>	VDS=40V, VGS=10V, ID=20A	-	16	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	4.8	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	4.4	-	
Switching Characteristics						
Turn-On Delay Time	t <sub>d(on)</sub>	VDD=40V, ID=20A, VGS=10V, R <sub>G</sub> =3Ω	-	8.0	-	nS
Rise Time	t <sub>r</sub>		-	5.6	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	14	-	
Fall Time	t <sub>f</sub>		-	4.8	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>		-	-	60	A
Reverse Recovery Time	Trr	Is=20 A,di/dt=100 A/μs, TJ=25℃	-	35	-	nS
Reverse Recovery Charge	Qrr		-	27.8	-	nC

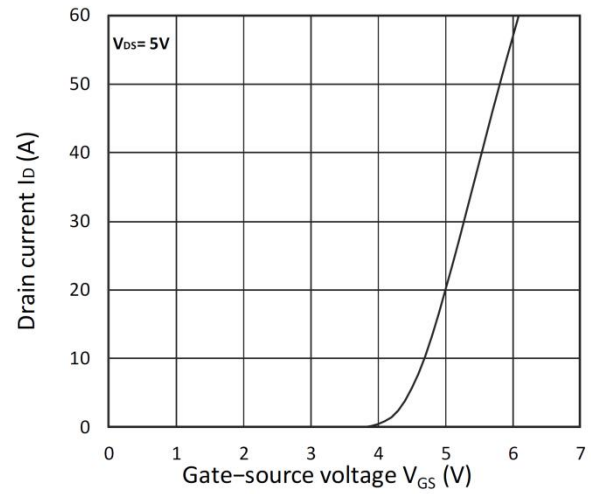
**Note :**

1. The test condition is  $V_{DD}=40V, V_{GS}=10V, L=0.5mH, R_G=25\Omega$

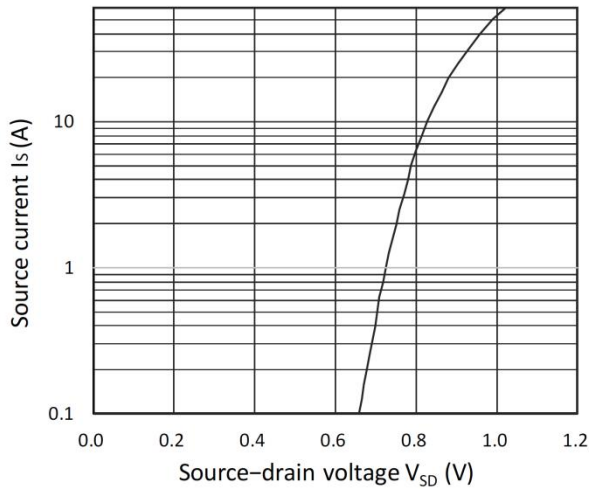
## Typical Characteristics



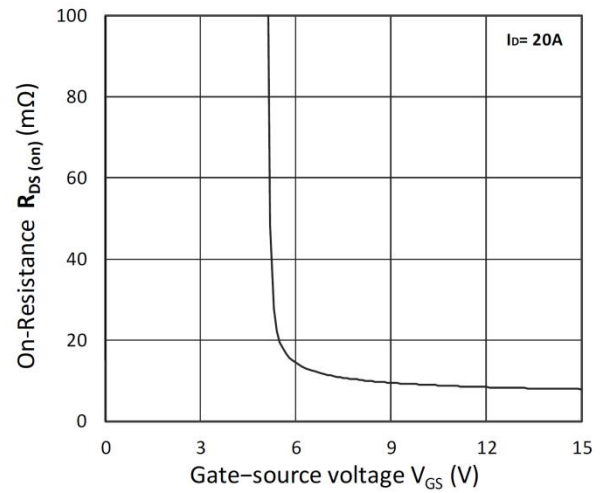
Output Characteristics



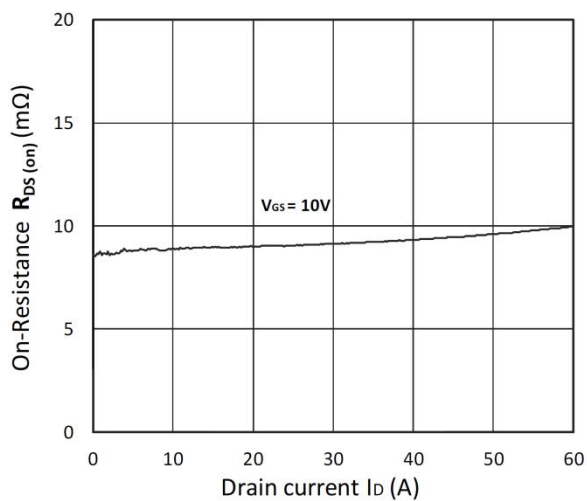
Transfer Characteristics



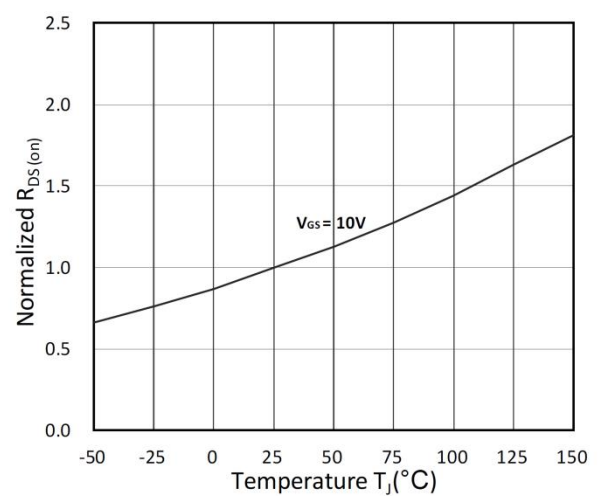
Forward Characteristics of Reverse



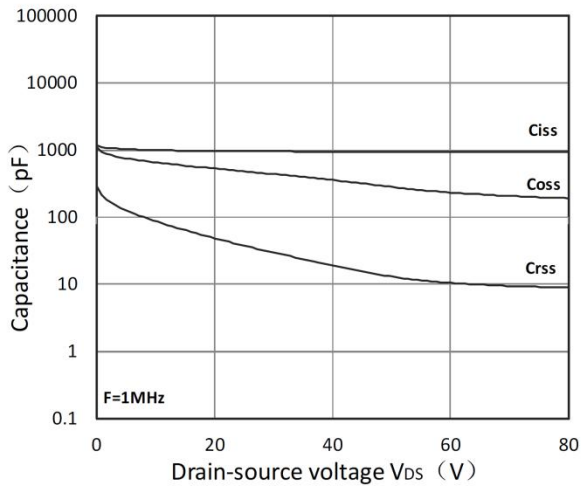
$R_{DS(on)}$  vs.  $V_{GS}$



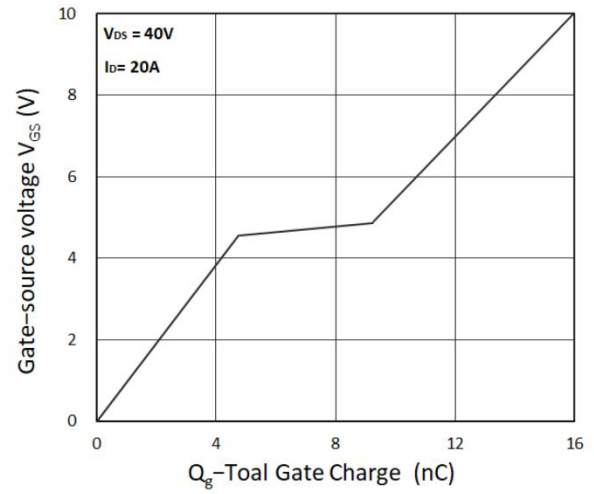
$R_{DS(on)}$  vs.  $I_D$



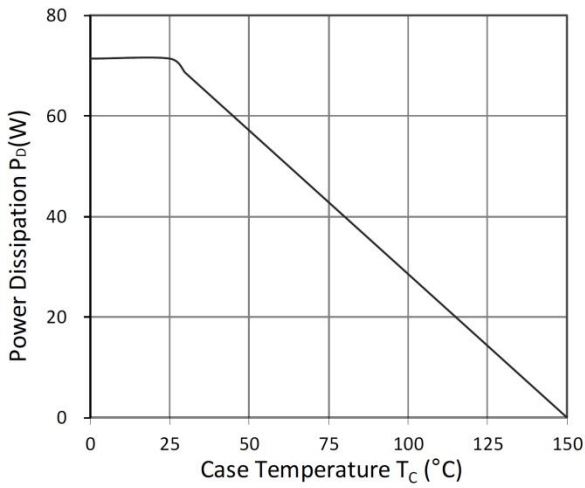
Normalized  $R_{DS(on)}$  vs. Temperature



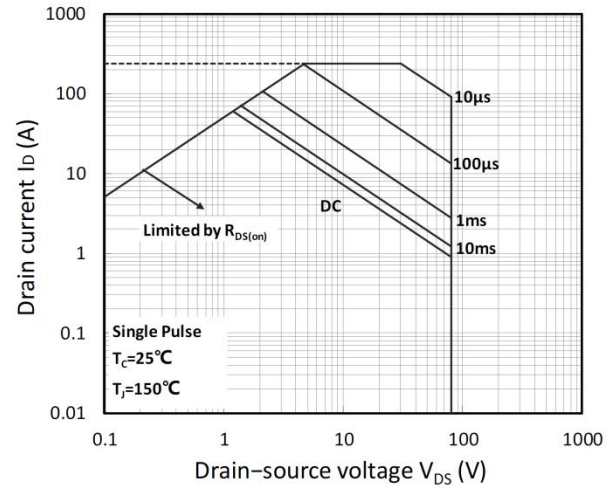
Capacitance Characteristics



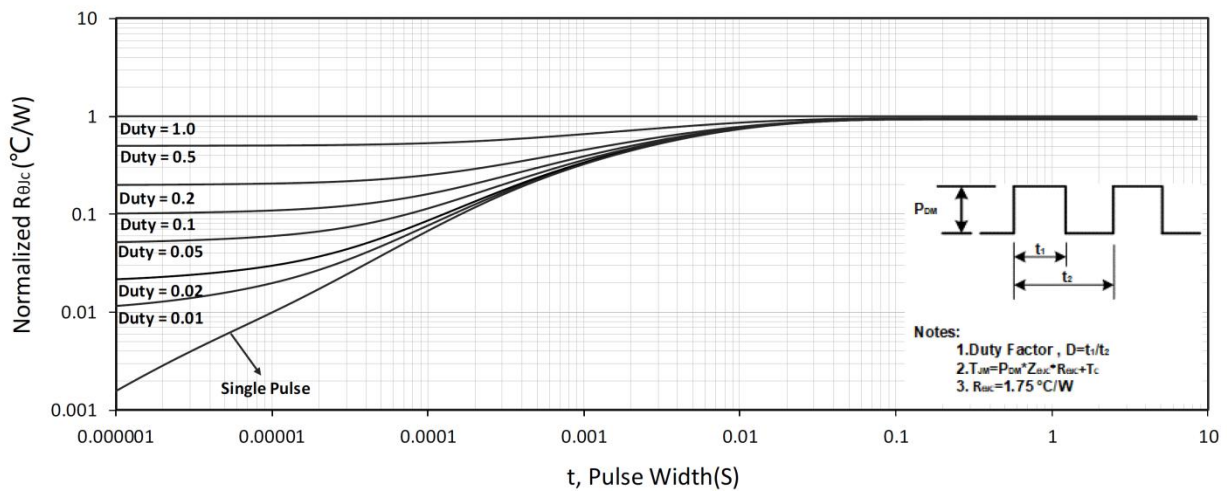
Gate Charge Characteristics



Power Dissipation

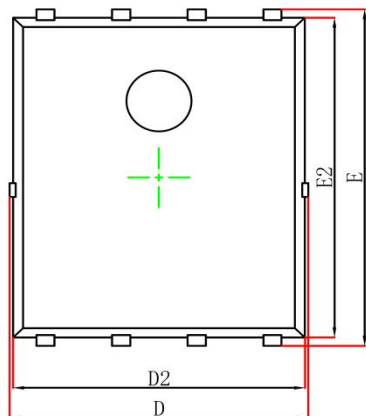


Safe Operating Area

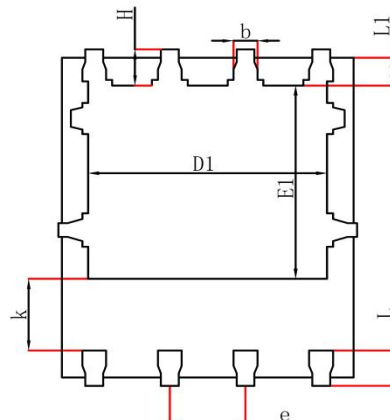


Normalized Maximum Transient Thermal Impedance

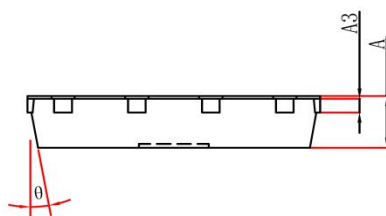
## PDFN5X6-8L Package Information



Top View  
[顶视图]



Bottom View  
[背视图]



Side View  
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
$\theta$	10°	12°	10°	12°